Vincotech

10-E112PNA080J101-L929C76Z
datasheet

***flow*PIM E1** **1200 V / 80 mΩ**

Topology features

- Converter+Inverter
- Open Emitter configuration
- SiC MOSFET
- Temperature sensor

Component features

- High Blocking Voltage with low drain source on state resistance
- High speed SiC-MOSFET technology
- Resistant to Latch-up

Housing features

- Base isolation: Al_2O_3
- Convex shaped substrate for superior thermal contact
- Compact housing
- CTI600 housing material
- Thermo-mechanical push-and-pull force relief
- Solder pin

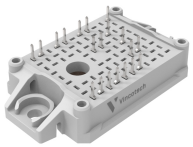
Target applications

- Embedded Drives
- HVAC
- Industrial Drives

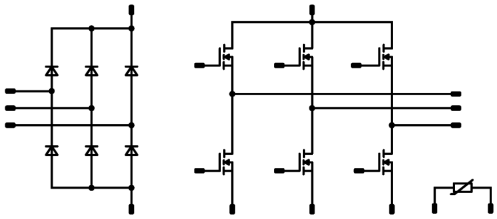
Types

- 10-E112PNA080J101-L929C76Z

flow E1 12 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Inverter Switch				
Drain-source voltage	V_{DSS}		1200	V
Drain current (DC current)	I_D	$T_j = T_{jmax}$ T_s = 80 °C	28	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}	68	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	66	W
Gate-source voltage	V_{GSS}	static	0 / 18	V
		dynamic	-5 / 22	V
Maximum Junction Temperature	T_{jmax}		175	°C
Rectifier Diode				
Peak repetitive reverse voltage	V_{RRM}		1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ T_s = 80 °C	45	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms T_j = 150 °C	200	A
Surge current capability	I^2t		200	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	64	W
Maximum junction temperature	T_{jmax}		175	°C
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…+(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
Creepage distance			>12,7	mm
Clearance			>12,7	mm
Comparative Tracking Index	CTI		≥ 600	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Switch										
Static										
Drain-source on-state resistance	$r_{DS(on)}$		18		15	25 125 150		71,7 77,2 83,7	110(1)	mΩ
Gate-source threshold voltage	$V_{GS(th)}$				0,0015	25	3,6	4,6	5,6	V
Gate to Source Leakage Current	I_{GSS}		22	0		25			200	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	1200		25			50	µA
Internal gate resistance	r_g							3		Ω
Short-circuit input capacitance	C_{iss}		0	10	0	25		2000		pF
Reverse transfer capacitance	C_{rss}							46		
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 5,2 W/mK (PTM)						1,45		K/W

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 1 Ω R_{goff} = 1 Ω	0/18	600	16	25 125 150		16,01 14,51 14,47		ns
Rise time	t_r					25 125 150		5,48 5,94 5,72		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		29,62 31,48 31,96		ns
Fall time	t_f					25 125 150		5,44 5,1 4,96		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,129 µC Q_{rFWD}=0,29 µC Q_{rFWD}=0,356 µC				25 125 150		0,22 0,247 0,263		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,031 0,029 0,029		mWs
Peak recovery current	I_{RRM}	di/dt=3120 A/µs di/dt=3136 A/µs di/dt=3390 A/µs				25 125 150		14,36 15,98 17,55		A
Reverse recovery time	t_{rr}					25 125 150		15,4 31,02 29,75		ns
Recovered charge	Q_r					25 125 150		0,129 0,29 0,356		µC
Reverse recovered energy	E_{rec}					25 125 150		0,016 0,095 0,125		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		2245,92 1632,16 4558,82		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Rectifier Diode										
Static										
Forward voltage	V_F				18	25 125 150		1,12 1,06 1,05	1,5(1)	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			50 1000	µA
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 5,2 W/mK (PTM)						1,48		K/W
Thermistor										
Static										
Rated resistance	R					25		5		kΩ
Deviation of R100	$\Delta_{R/R}$	R_{100} = 499 Ω				100	3,2		3,3	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,3		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3380		K
Vincotech Thermistor Reference									V	

(1) Value at chip level

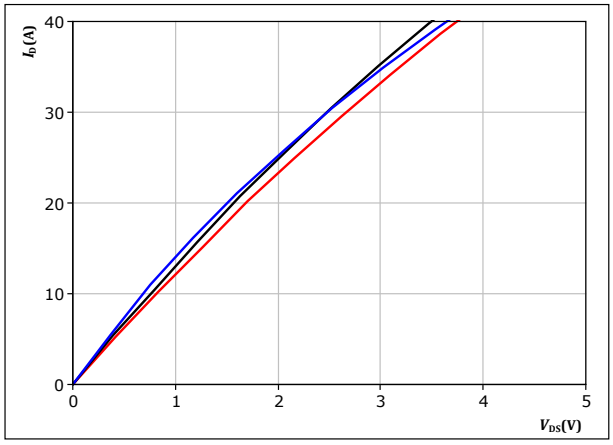
(2) Only valid with pre-applied Vincotech thermal interface material.

Inverter Switch Characteristics

figure 1. **MOSFET**

Typical output characteristics

$I_D = f(V_{DS})$

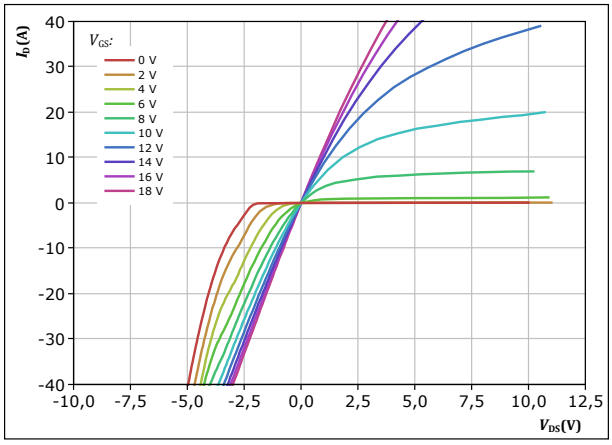


t_p =	250	µs		
V_{GS} =	18	V	T_j:	25 °C
				125 °C
				150 °C

figure 2. **MOSFET**

Typical output characteristics

$I_D = f(V_{DS})$



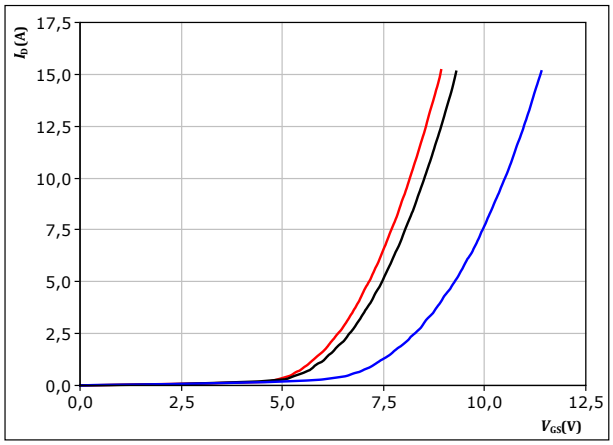
t_p =	250	µs
T_j =	150	°C

V_{GS} from 0 V to 18 V in steps of 2 V

figure 3. **MOSFET**

Typical transfer characteristics

$I_D = f(V_{GS})$

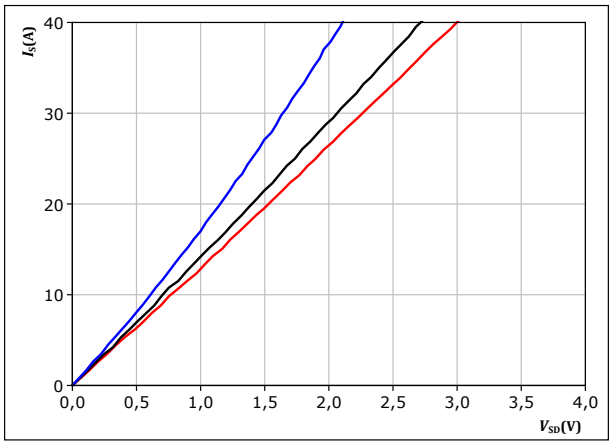


t_p =	250	µs		
V_{DS} =	10	V	T_j:	25 °C
				125 °C
				150 °C

figure 4. **MOSFET**

Typical reverse drain current characteristics

$I_{SD} = f(V_{SD})$



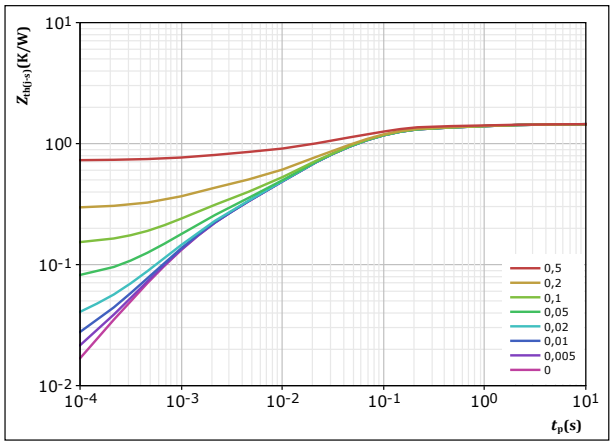
t_p =	250	µs		
V_{GS} =	18	V	T_j:	25 °C
				125 °C
				150 °C

Inverter Switch Characteristics

figure 5. **MOSFET**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D =$ t_p / T

$R_{th(j-s)} =$ 1,448 K/W

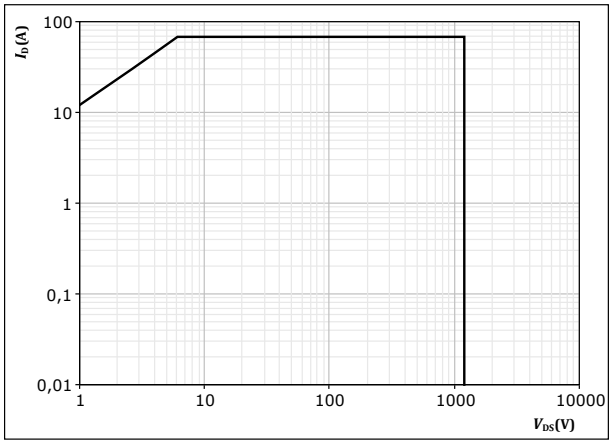
MOSFET thermal model values

R (K/W)	τ (s)
3,14E-02	4,56E+00
1,15E-01	7,55E-01
7,55E-01	6,16E-02
3,79E-01	1,32E-02
1,71E-01	1,29E-03

figure 6. **MOSFET**

Safe operating area

$I_D = f(V_{DS})$



$D =$ single pulse

$T_s =$ 80 °C

$V_{GS} =$ 18 V

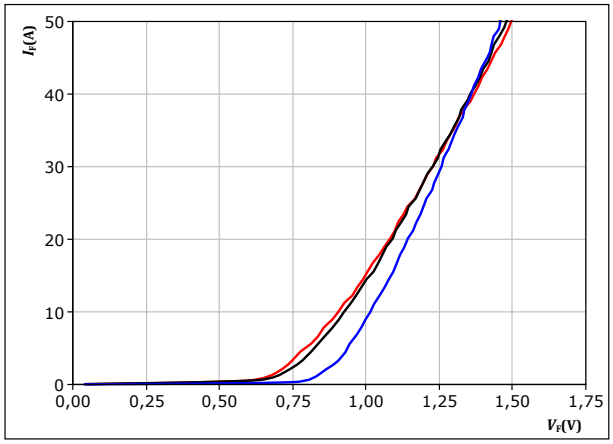
$T_j =$ T_{jmax}

Rectifier Diode Characteristics

figure 7. **Rectifier**

Typical forward characteristics

$I_F = f(V_F)$



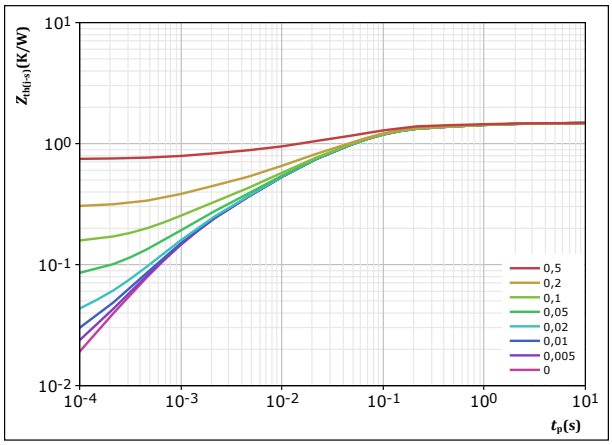
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 8. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,482 K/W

Rectifier thermal model values

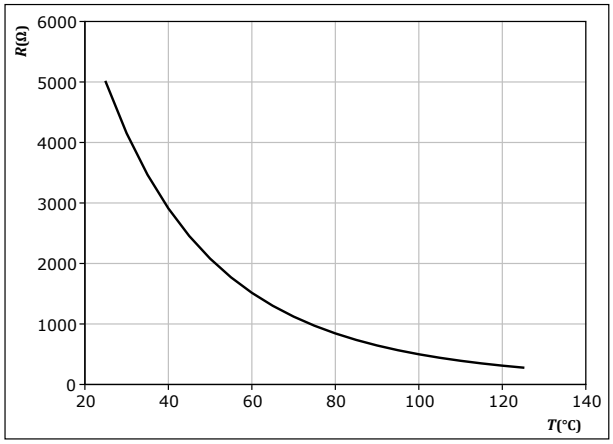
R (K/W)	τ (s)
4,21E-02	5,03E+00
1,49E-01	5,66E-01
7,66E-01	5,69E-02
3,76E-01	9,10E-03
1,54E-01	1,08E-03

Thermistor Characteristics

figure 9. **Thermistor**

Typical NTC characteristic as function of temperature

$R_T = f(T)$

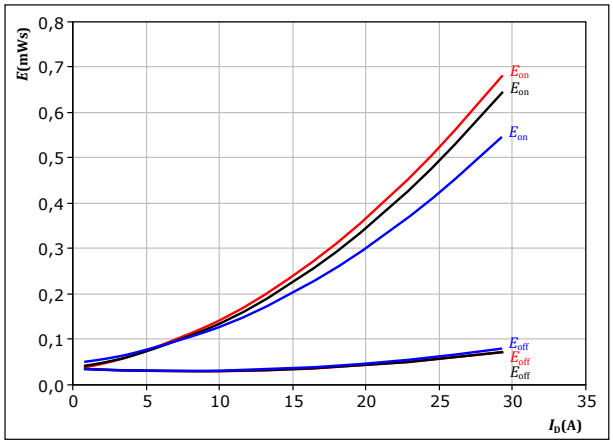


Inverter Switching Characteristics

figure 10. **MOSFET**

Typical switching energy losses as a function of drain current

$E = f(I_D)$



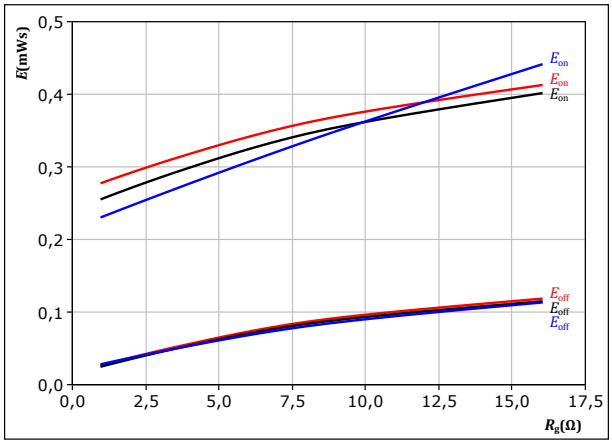
With an inductive load at

V_{DS} =	600	V	T_j: 25 °C
V_{GS} =	0/18	V	125 °C
R_{gon} =	1	Ω	150 °C
R_{goff} =	1	Ω	

figure 11. **MOSFET**

Typical switching energy losses as a function of MOSFET turn on gate resistor

$E = f(R_g)$



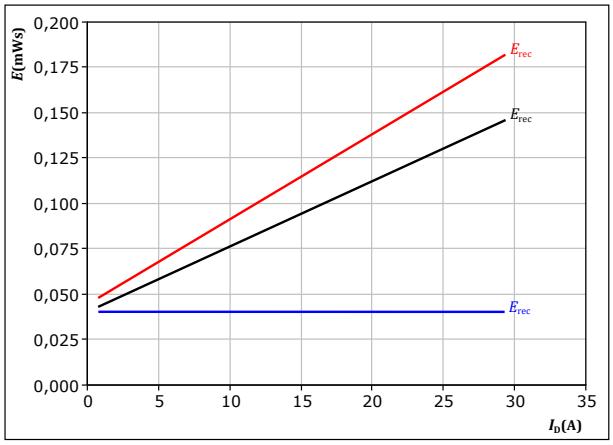
With an inductive load at

V_{DS} =	600	V	T_j: 25 °C
V_{GS} =	0/18	V	125 °C
I_D =	16	A	150 °C

figure 12. **MOSFET**

Typical reverse recovered energy loss as a function of drain current

$E_{rec} = f(I_D)$



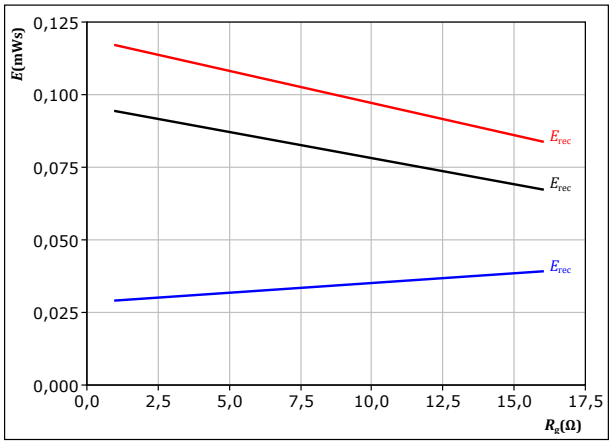
With an inductive load at

V_{DS} =	600	V	T_j: 25 °C
V_{GS} =	0/18	V	125 °C
R_{gon} =	1	Ω	150 °C

figure 13. **MOSFET**

Typical reverse recovered energy loss as a function of MOSFET turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

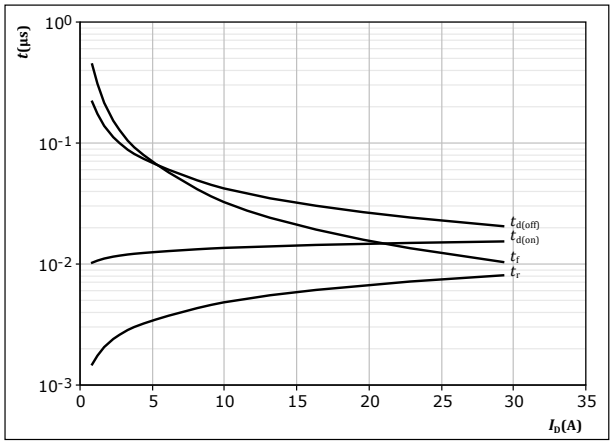
V_{DS} =	600	V	T_j: 25 °C
V_{GS} =	0/18	V	125 °C
I_D =	16	A	150 °C

Inverter Switching Characteristics

figure 14. **MOSFET**

Typical switching times as a function of drain current

t = f(I_D)



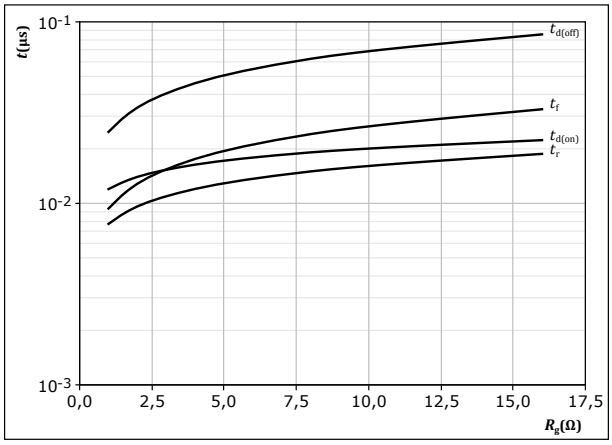
With an inductive load at

T_j =	150	°C
V_{DS} =	600	V
V_{GS} =	0/18	V
R_{gon} =	1	Ω
R_{goff} =	1	Ω

figure 15. **MOSFET**

Typical switching times as a function of MOSFET turn on gate resistor

t = f(R_g)



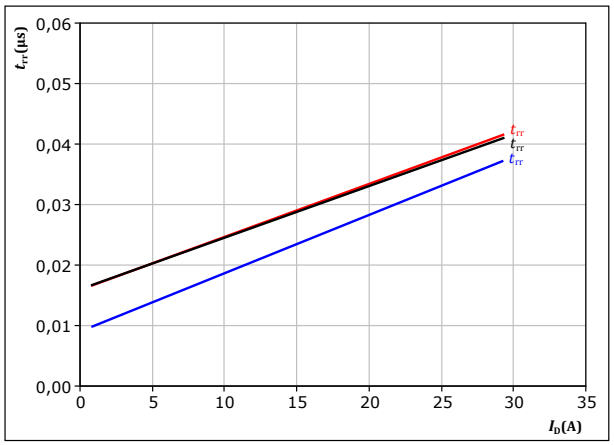
With an inductive load at

T_j =	150	°C
V_{DS} =	600	V
V_{GS} =	0/18	V
I_D =	16	A

figure 16. **MOSFET**

Typical reverse recovery time as a function of drain current

t_{rr} = f(I_D)



At

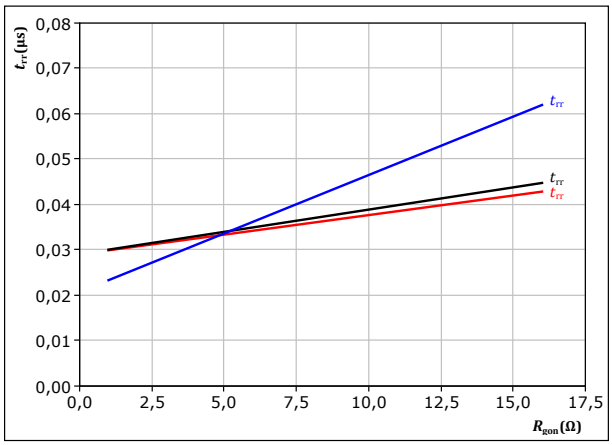
V_{DS} =	600	V
V_{GS} =	0/18	V
R_{gon} =	1	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 17. **MOSFET**

Typical reverse recovery time as a function of MOSFET turn on gate resistor

t_{rr} = f(R_{gon})



At

V_{DS} =	600	V
V_{GS} =	0/18	V
I_D =	16	A

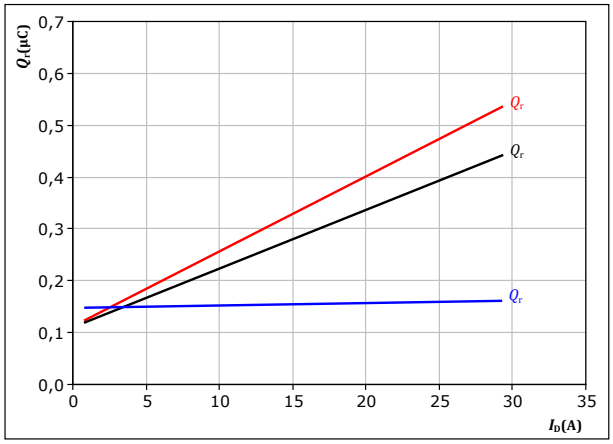
T_j: 25 °C, 125 °C, 150 °C

Inverter Switching Characteristics

figure 18. **MOSFET**

Typical recovered charge as a function of drain current

$Q_r = f(I_D)$

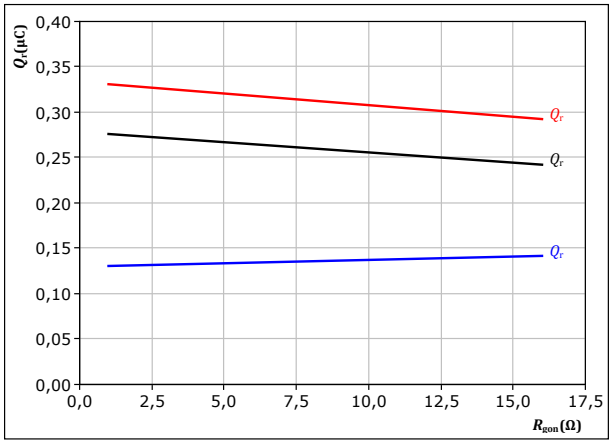


At	V_{DS} =	600	V		
	V_{GS} =	0/18	V	T_j:	25 °C
	R_{gon} =	1	Ω		125 °C
					150 °C

figure 19. **MOSFET**

Typical recovered charge as a function of MOSFET turn on gate resistor

$Q_r = f(R_{gon})$

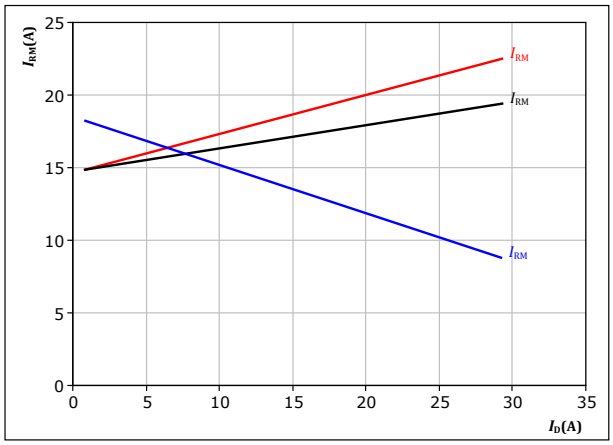


At	V_{DS} =	600	V		
	V_{GS} =	0/18	V	T_j:	25 °C
	I_D =	16	A		125 °C
					150 °C

figure 20. **MOSFET**

Typical peak reverse recovery current as a function of drain current

$I_{RM} = f(I_D)$

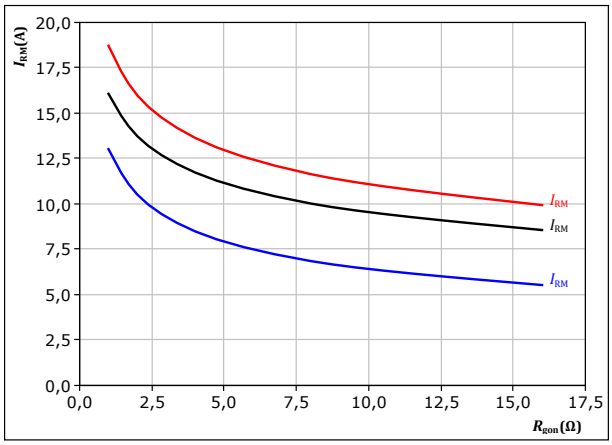


At	V_{DS} =	600	V		
	V_{GS} =	0/18	V	T_j:	25 °C
	R_{gon} =	1	Ω		125 °C
					150 °C

figure 21. **MOSFET**

Typical peak reverse recovery current as a function of MOSFET turn on gate resistor

$I_{RM} = f(R_{gon})$



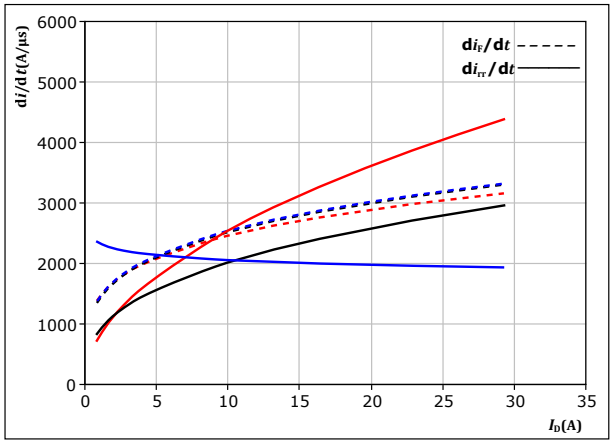
At	V_{DS} =	600	V		
	V_{GS} =	0/18	V	T_j:	25 °C
	I_D =	16	A		125 °C
					150 °C

Inverter Switching Characteristics

figure 22. **MOSFET**

Typical rate of fall of forward and reverse recovery current as a function of drain current

di_F/dt, di_{rr}/dt = f(I_D)

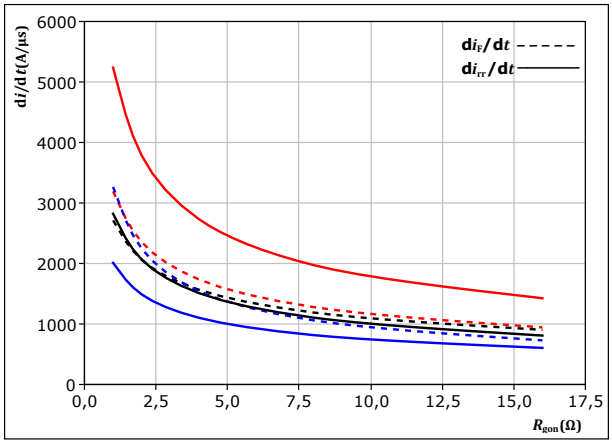


At				
V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	0/18	V		125 °C
R_{gon} =	1	Ω		150 °C

figure 23. **MOSFET**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})

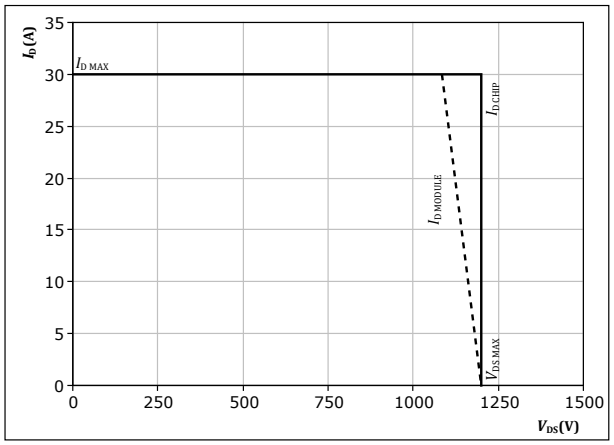


At				
V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	0/18	V		125 °C
I_D =	16	A		150 °C

figure 24. **MOSFET**

Reverse bias safe operating area

I_D = f(V_{DS})



At			
T_j =	150	°C	
R_{gon} =	1	Ω	
R_{goff} =	1	Ω	

Inverter Switching Definitions

figure 25. **MOSFET**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})

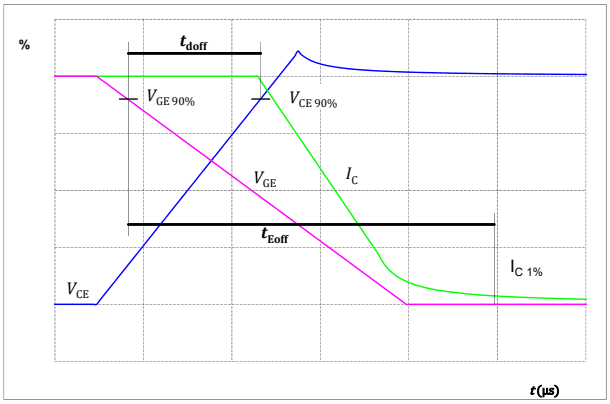


figure 26. **MOSFET**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})

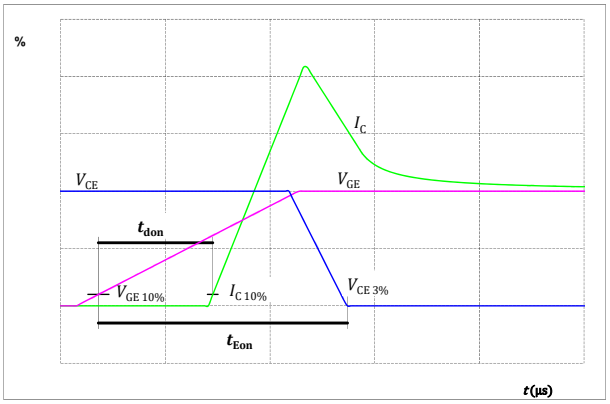


figure 27. **MOSFET**

Turn-off Switching Waveforms & definition of t_f

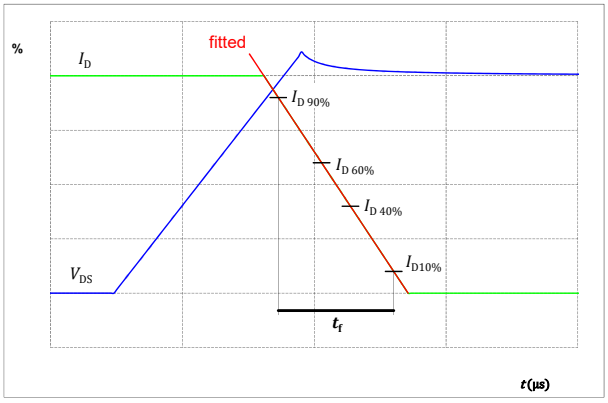
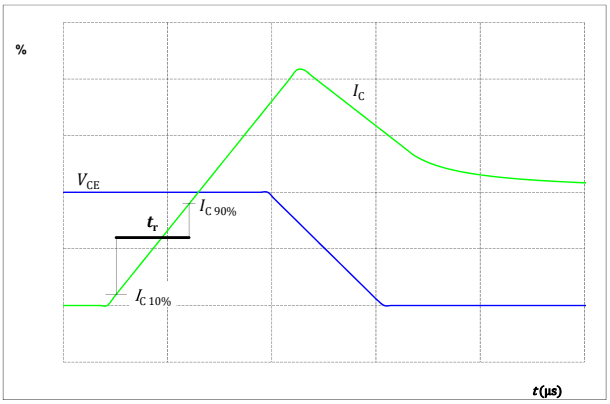


figure 28. **MOSFET**

Turn-on Switching Waveforms & definition of t_r



Inverter Switching Definitions

figure 29. **FWD**

Turn-off Switching Waveforms & definition of t_{trr}

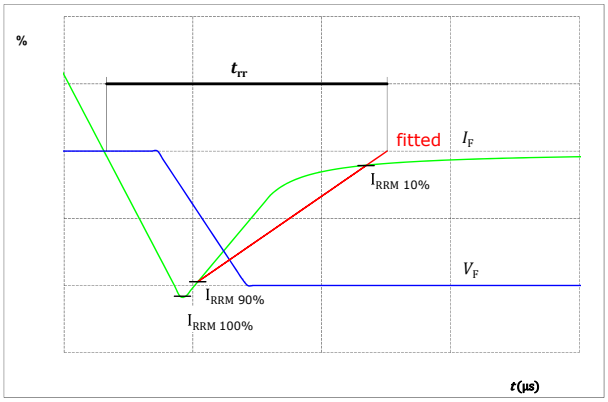


figure 30. **FWD**

Turn-on Switching Waveforms & definition of t_{Qrr} (t_{Qrr} = integrating time for Q_{rr})

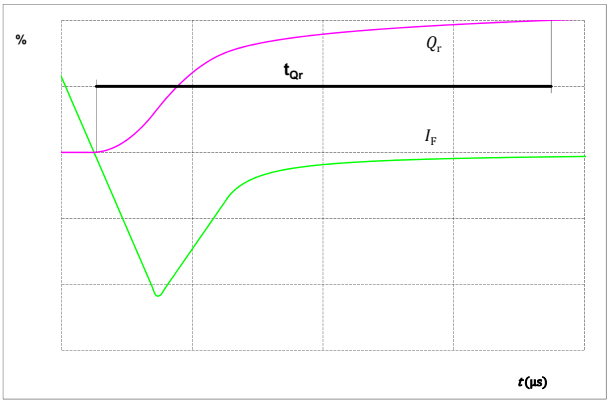
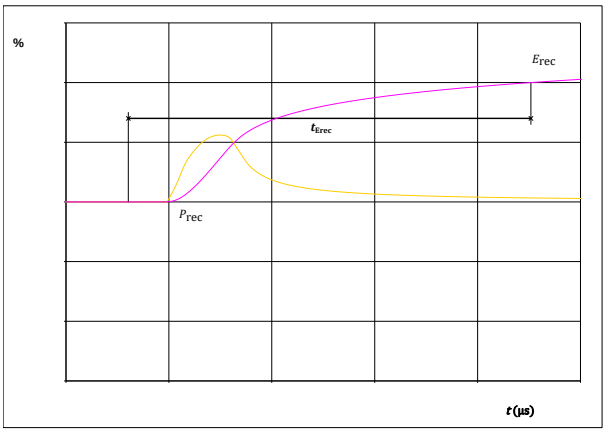


figure 31. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})



Vincotech

10-E112PNA080J101-L929C76Z
datasheet

Ordering Code

Version	Ordering Code
Without thermal paste	10-E112PNA080J101-L929C76Z
With thermal paste (5,2 W/mK, PTM6000HV)	10-E112PNA080J101-L929C76Z-/7/

Marking

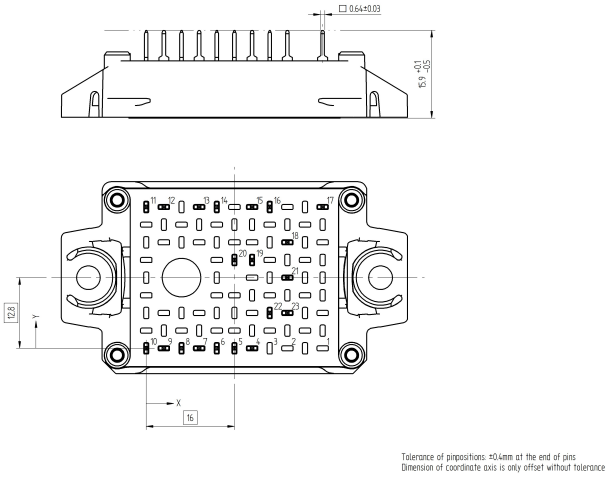


	Name		Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
	TTTTTTVV	LLLLL	SSSS	WWYY		

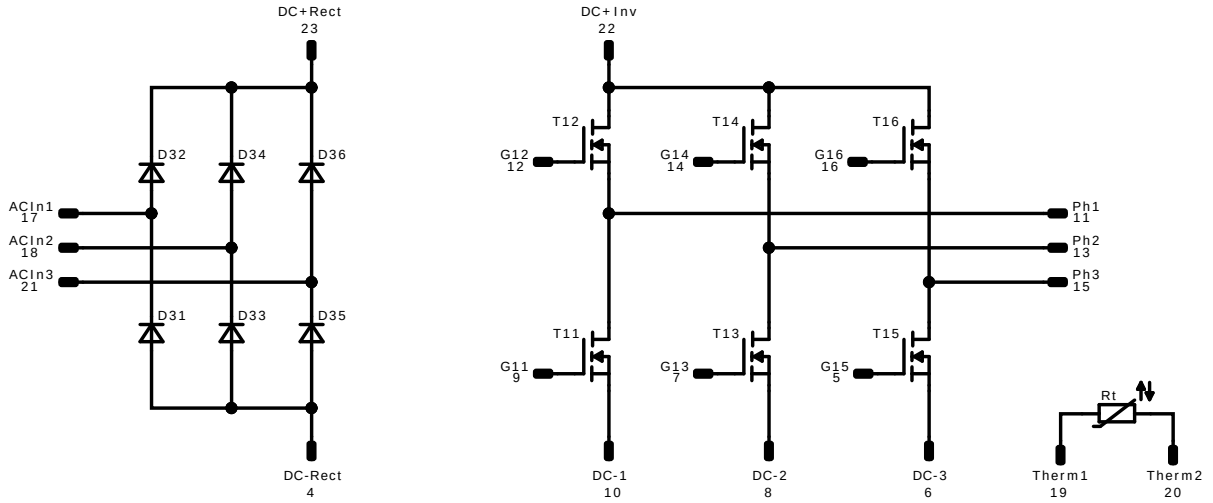
Outline

Pin table [mm]

Pin	X	Y	Function
1	not assembled		
2	not assembled		
3	not assembled		
4	19,2	0	DC-Rect
5	16	0	G15
6	12,8	0	DC-3
7	9,6	0	G13
8	6,4	0	DC-2
9	3,2	0	G11
10	0	0	DC-1
11	0	25,6	Ph1
12	3,2	25,6	G12
13	9,6	25,6	Ph2
14	12,8	25,6	G14
15	19,2	25,6	Ph3
16	22,4	25,6	G16
17	32	25,6	ACIn1
18	25,6	19,2	ACIn2
19	19,2	16	Therm1
20	16	16	Therm2
21	25,6	12,8	ACIn3
22	22,4	6,4	DC+Inv
23	25,6	6,4	DC+Rect



Pinout



Identification					
ID	**Component**	**Voltage**	**Current**	**Function**	**Comment**
T11, T12, T13, T14, T15, T16	MOSFET	1200 V	80 mΩ	Inverter Switch	
D31, D32, D33, D34, D35, D36	Rectifier	1600 V	18 A	Rectifier Diode	
Rt	NTC			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* E1 packages see vincotech.com website.

Package data
Package data for *flow* E1 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is UL 1557 recognized under E192116 up to a junction temperature under switching condition $T_{j,op}$=175°C and up to 3500VAC/1min isolation voltage. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-E112PNA080J101-L929C76Z-D1-14	3 Nov. 2026	Initial Release	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.